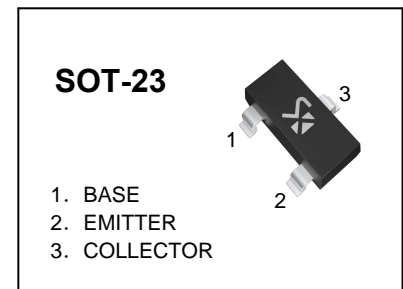


## PNP Silicon Epitaxial Planar Transistor

For switching and amplifier applications.  
Especially suitable for AF-driver stages and  
low power output stages.



**MARKING:** Y2

### MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-25	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-1000	mA
$P_C$	Collector Power Dissipation	1000	mW
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}$ , $I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$ , $I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1\text{mA}$ , $I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -35\text{V}$ , $I_E = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4\text{V}$ , $I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -1\text{V}$ , $I_C = -100\text{mA}$	85		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800\text{mA}$ , $I_B = -80\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800\text{mA}$ , $I_B = -80\text{mA}$			-1.2	V
Transition frequency	$f_T$	$V_{CE} = -6\text{V}$ , $I_C = -20\text{mA}$ $f = 30\text{MHz}$	150			MHz

## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

